

In the Specification:

Please rewrite the last paragraph on page 5 to read as follows:

Following creation of the mask, which can be done using conventional processes, doping is done, preferably an implantation of phosphorous ions at a dose of, for example,  $2 \times 10^{13}$  atoms/cm<sup>2</sup>, in order to create an n-doped trough 5 in the semiconductor substrate 1. The implantation energy in this process is such that over the trough 5 in the semiconductor substrate 1 there still remains a weakly p-doped inner area 6. At a dose of  $2 \times 10^{13}$  atoms/cm<sup>2</sup> this is, despite the back-scattered phosphorous ions, for example, the case if the implantation energy is 6 MeV phosphorous ions.